

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	NDS331N
▶ Overseas	Part Number	NDS331N-EV
▶ Equivalent	Part Number	NDS331N

EV is the abbreviation of name EVVO

N-Channel Enhancement Mode MOSFET

Description

The NDS331N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

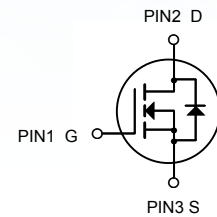
$V_{DS} = 20V$ $I_D = 2.3A$

$R_{DS(ON)} < 60m\Omega @ V_{GS}=4.5V$

Application

Battery protection
 Load switch
 Uninterruptible power supply

SOT-23



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	2.3	A
I_{DM}	Drain Current-Pulsed (Note 1)	16	A
P_D	Maximum Power Dissipation	0.9	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	139	$^\circ C/W$

N-Channel Enhancement Mode MOSFET

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=2.0A$	-	54	72	m Ω
		$V_{GS}=4.5V, I_D=2.3A$	-	48	60	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=2.3A$	-	8	-	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	260	-	PF
Output Capacitance	C_{oss}		-	48	-	PF
Reverse Transfer Capacitance	C_{rss}		-	27	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=3.3\Omega$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	2.5	-	nS
Turn-on Rise Time	t_r		-	3.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	21	-	nS
Turn-Off Fall Time	t_f		-	3	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=2.3A,$ $V_{GS}=4.5V$	-	2.9	5	nC
Gate-Source Charge	Q_{gs}		-	0.4	-	nC
Gate-Drain Charge	Q_{gd}		-	0.6	-	nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=2.3A$	-	0.75	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	3.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N-Channel Enhancement Mode MOSFET

Typical Electrical and Thermal Characteristics

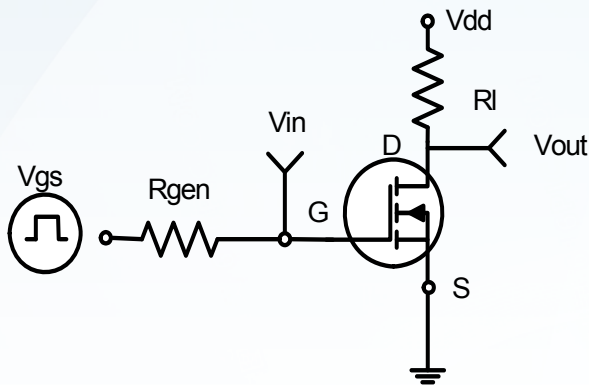


Figure 1: Switching Test Circuit

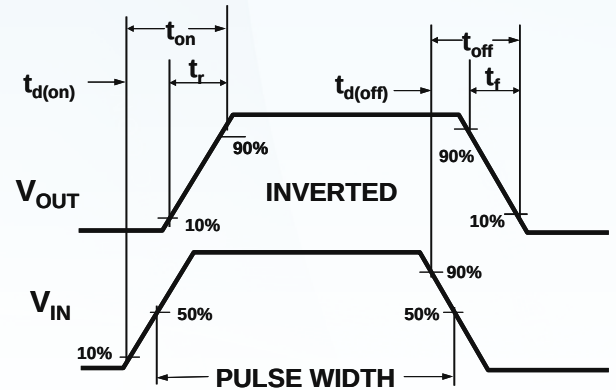


Figure 2: Switching Waveforms

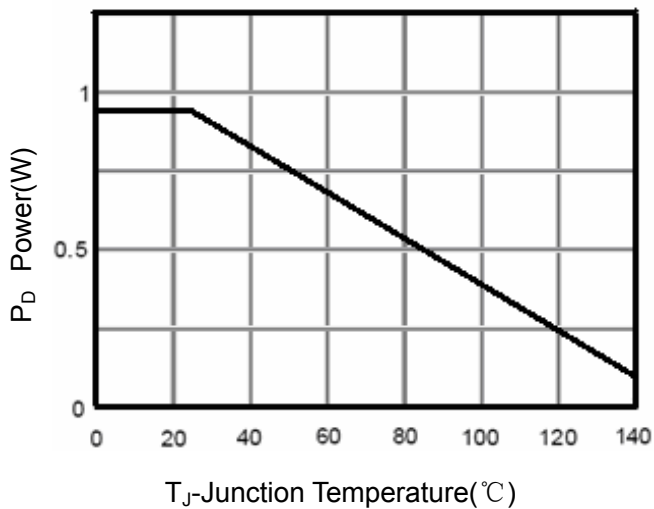


Figure 3 Power Dissipation

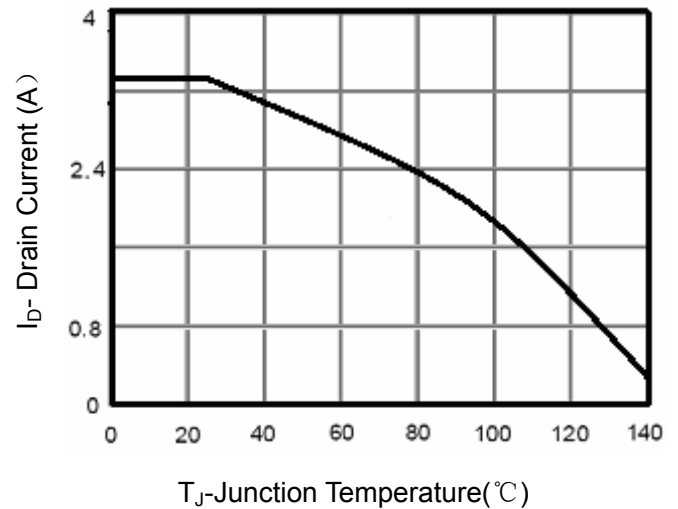


Figure 4 Drain Current

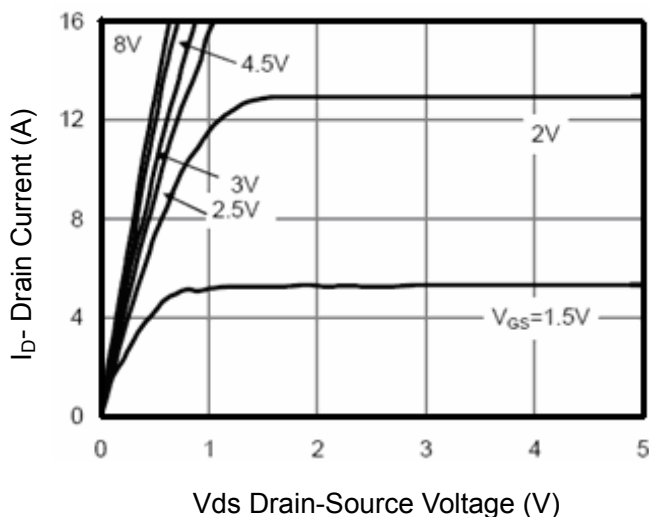


Figure 5 Output Characteristics

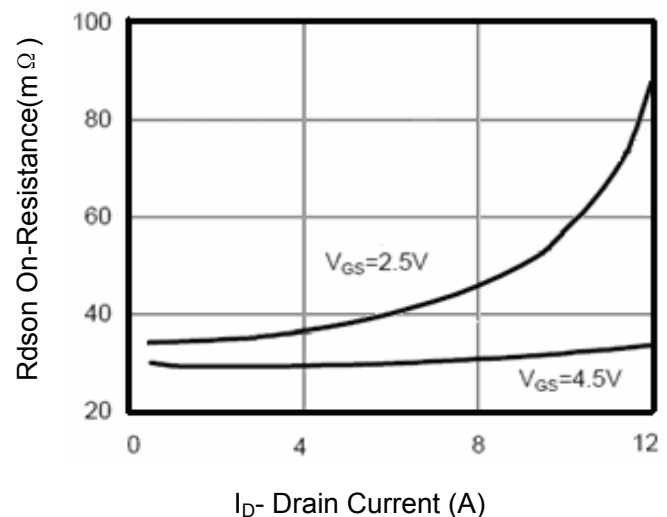


Figure 6 Drain-Source On-Resistance

N-Channel Enhancement Mode MOSFET

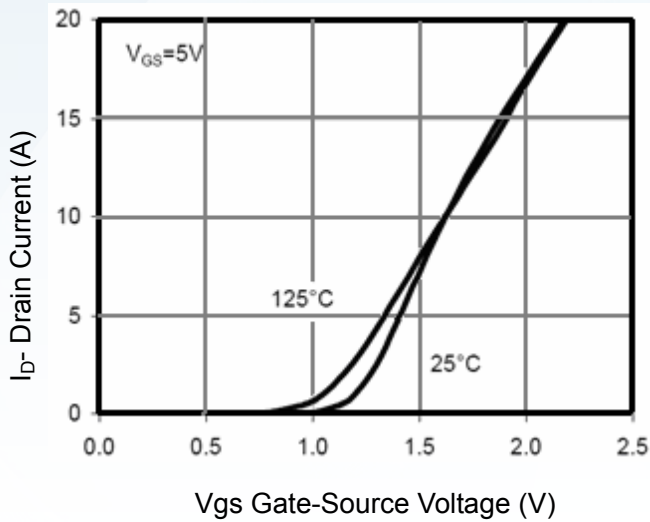


Figure 7 Transfer Characteristics

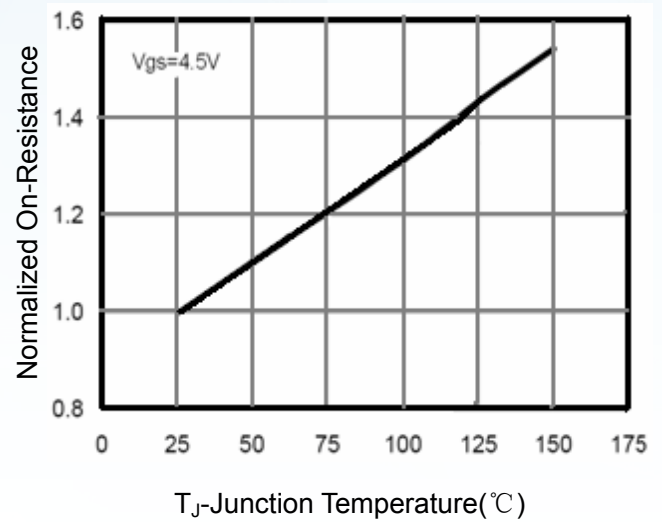


Figure 8 Drain-Source On-Resistance

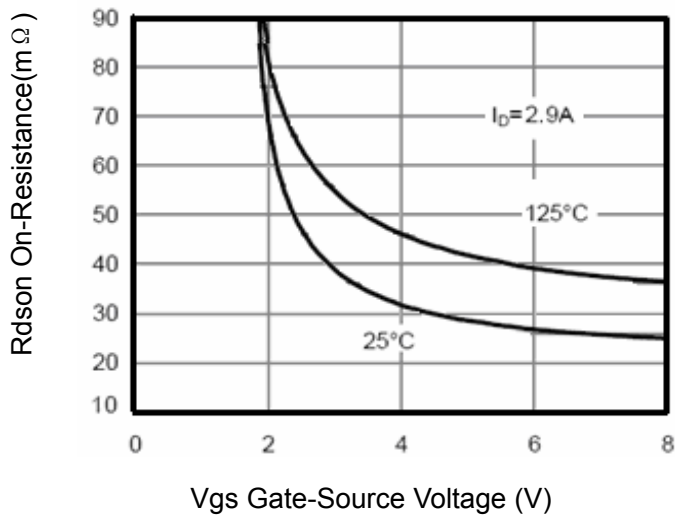


Figure 9 $R_{DS(on)}$ vs V_{GS}

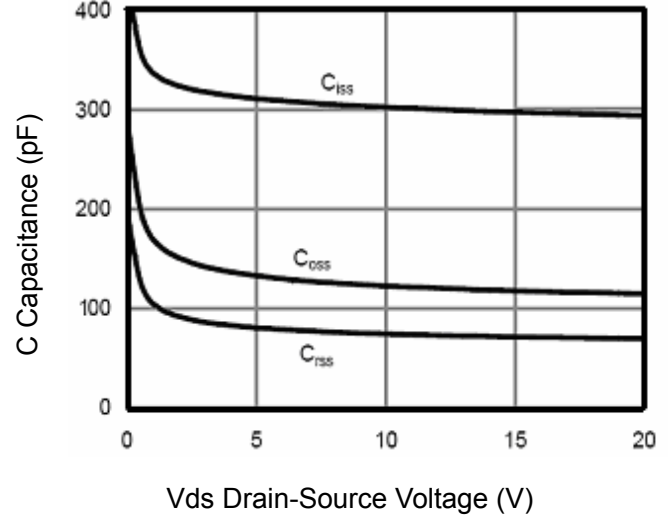


Figure 10 Capacitance vs V_{DS}

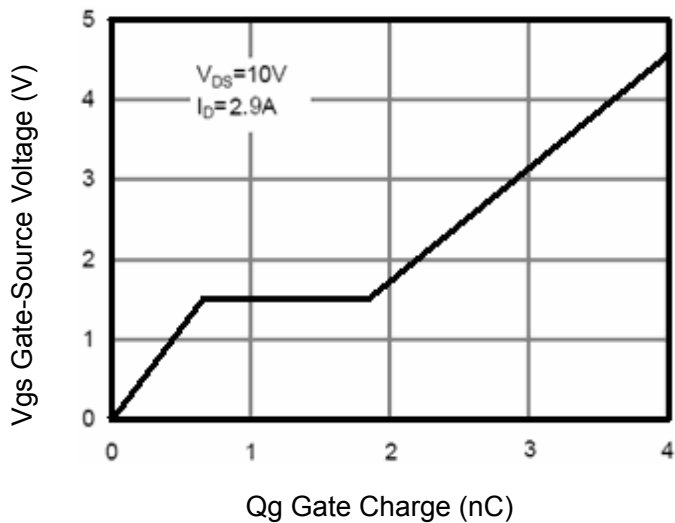


Figure 11 Gate Charge

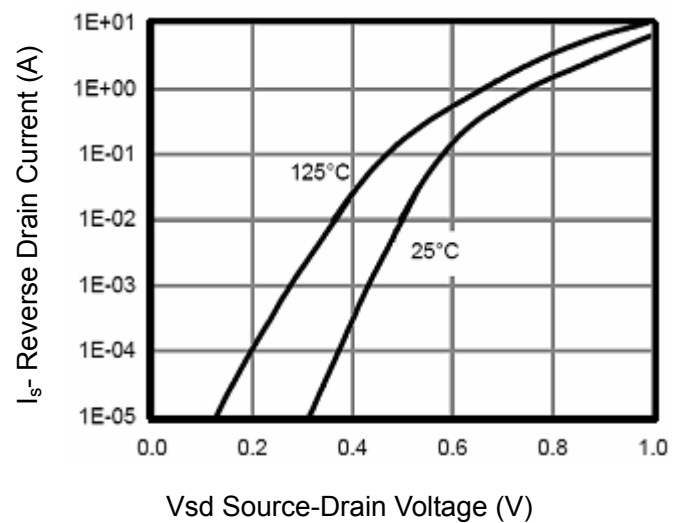
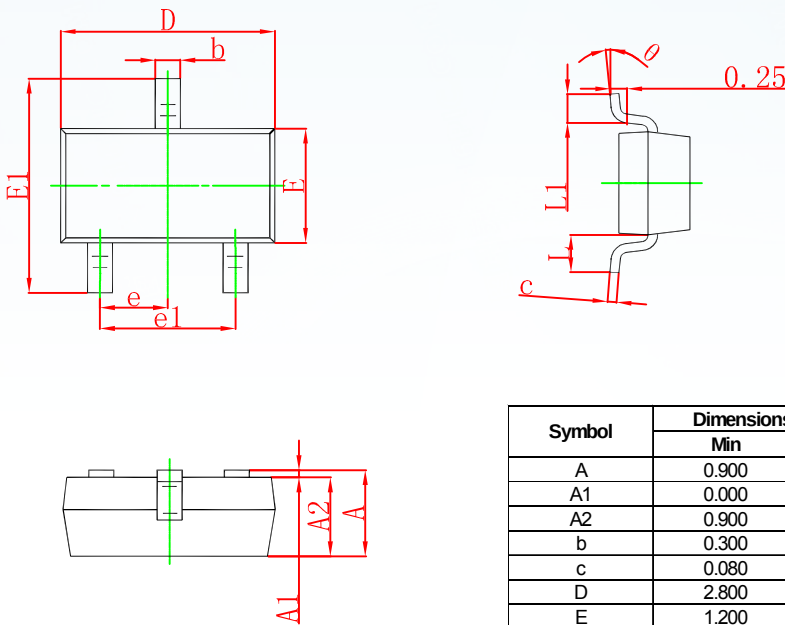


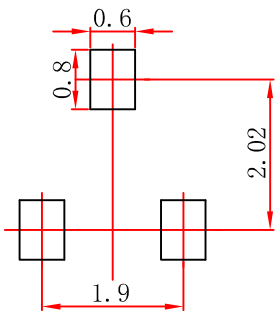
Figure 12 Source- Drain Diode Forward

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
NDS331N	SOT-23	331M	3000

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